

**TITLE: METHOD FOR PRODUCING A SEMICONDUCTOR STRUCTURE
COMPRISING AN INTERFACE REGION INCLUDING AGGLOMERATES**

Abstract

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The invention relates to a method for producing a semiconductor structure comprising the following steps: a) providing a working layer made of a semiconductor material; b) providing a carrier substrate made of a semiconductor material; c) depositing a film composed of a semiconductor material different from
10 that or those of the working layer and of the carrier substrate, having a thickness of less than 50 nm, on the free face to be joined of the working layer and/or on the free face to be joined of the carrier substrate; d) forming an intermediate structure, comprising directly joining, along a bonding interface extending along a main plane, the free faces to be joined of the working layer and of the carrier
15 substrate, respectively, the intermediate structure comprising an encapsulated film originating from the one or more films deposited in step c); e) annealing the intermediate structure at a temperature higher than or equal to a critical temperature, so as to bring about segmentation of the encapsulated film and form the semiconductor structure comprising an interface region between the working
20 layer and the carrier substrate, said interface region comprising: - regions of direct contact between the working layer and the carrier substrate; and - agglomerates comprising the semiconductor material of the film, and having a thickness, along an axis normal to the main plane, of less than or equal to 250 nm; the regions of direct contact and the agglomerates being adjacent in the main plane.

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Fig. 1